

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

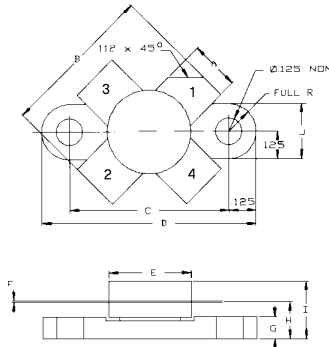
The **ASI SD1019-02** is Designed for VHF Communications up to 136 MHz

FEATURES:

- $P_G = 4.5$ dB Minimum at 150 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	117 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	1.7 $^\circ C/W$

PACKAGE STYLE .380 4 LEAD FLG


	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.200/5.08	.230/5.84
B	.785/19.94	
C	.778/19.79	.738/18.74
D	.970/24.64	.960/24.39
E		.305/7.78
F	.004/0.10	.006/0.15
G	.090/2.29	.105/2.67
H	.160/4.06	.188/4.77
I		.030/7.62
J	.242/6.11	.255/6.48

1 = COLLECTOR 3 & 4 = EMITTER 2 = BASE

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA			65			V
BV_{CEO}	$I_C = 200$ mA			35			V
BV_{EBO}	$I_E = 10$ mA			4.0			V
I_{CBO}	$V_{CB} = 30$ V				1.5		mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 500$ mA		5.0			---
C_{OB}	$V_{CB} = 30$ V	$f = 1.0$ MHz				150	pF
P_{OUT}	$V_{CC} = 13.5$ V	$P_{IN} = 10.6$ W	$f = 150$ MHz	30			W
P_G				4.5			dB